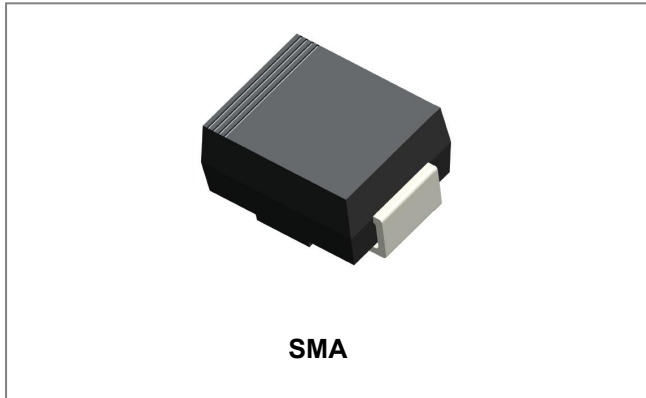


GS1A THRU GS1M

1.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb – Free Device
- “-HF” suffix is for Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SMA molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.06 grams

Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	GS1A	GS1B	GS1D	GS1G	GS1J	GS1K	GS1M	Units	
Peak Repetitive Reverse Voltage	V_{RRM}									
Working Peak Reverse Voltage	V_{RWM}	50	100	200	400	600	800	1000	V	
DC Blocking Voltage	V_R									
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V	
Average Rectified Output Current @ $T_L = 100^\circ\text{C}$	I_O	1.0								A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30								A
Forward Voltage @ $I_F = 1.0\text{ A}$	V_F	1.10								V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$	I_{RM}	5.0 200								μA
Reverse Recovery Time(Note1)	t_{rr}	2.5								μS
Typical Junction Capacitance(Note2)	C_J	15								pF
Typical Thermal Resistance Junction to Lead (Note 3)	$R_{\theta JL}$	30								$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +175								$^\circ\text{C}$

Note: 1. Reverse recovery condition $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{rr}=0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. Mounted on P.C.B. with 8.0mm² land areas.

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Ratings and Characteristics Curves

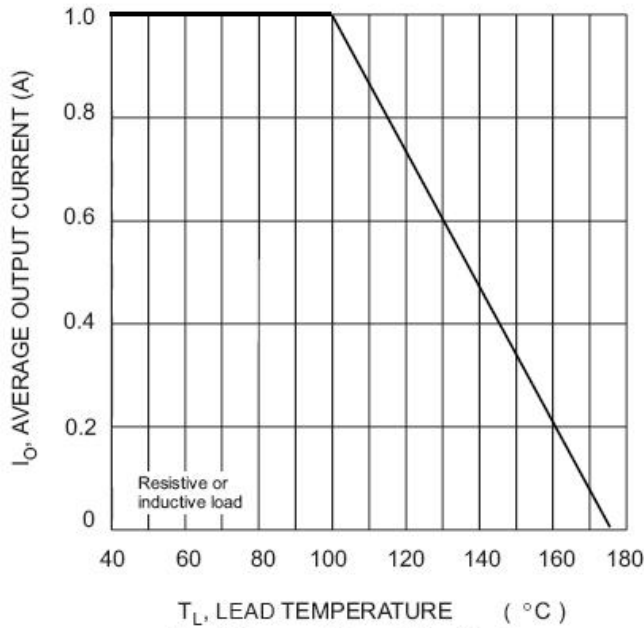


Fig. 1 Forward Current Derating Curve

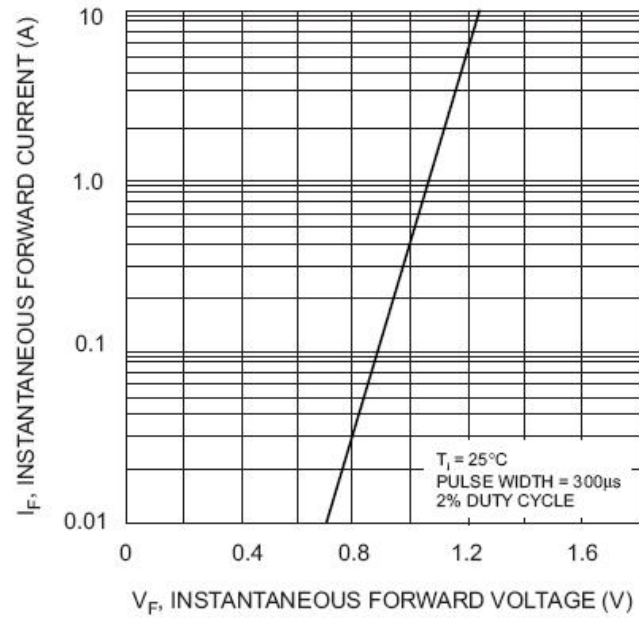


Fig. 2 Typical Forward Characteristics

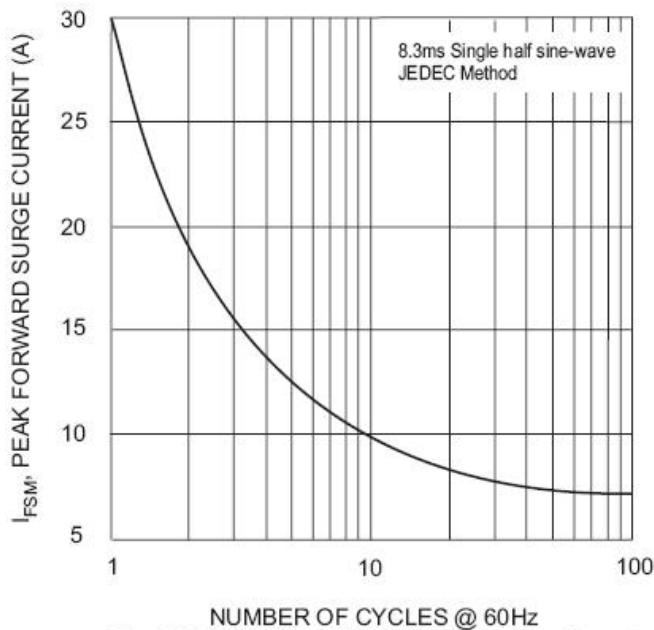


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

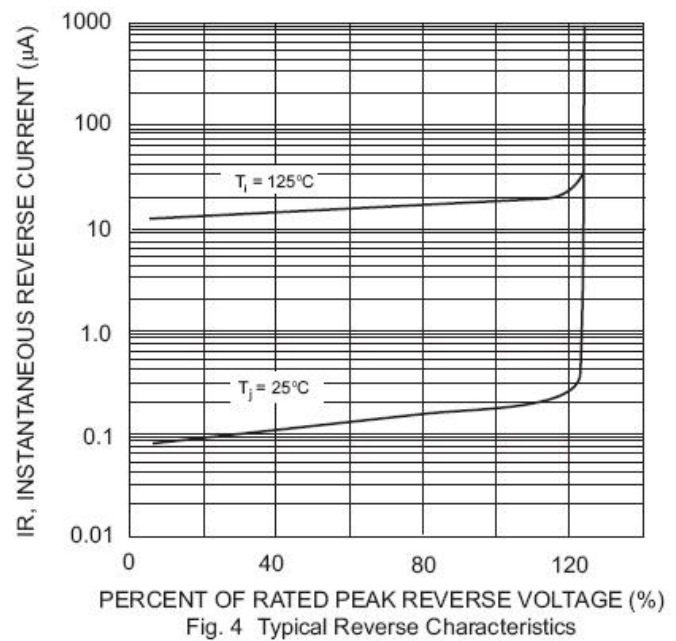
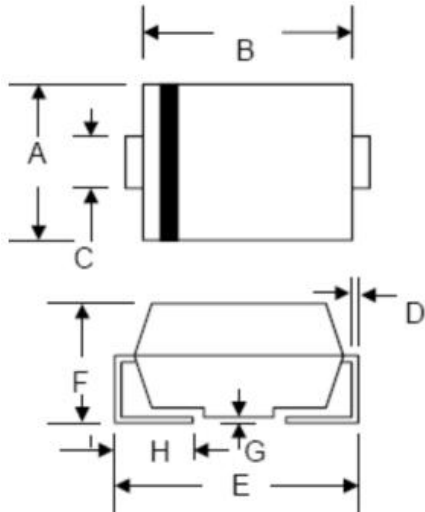


Fig. 4 Typical Reverse Characteristics

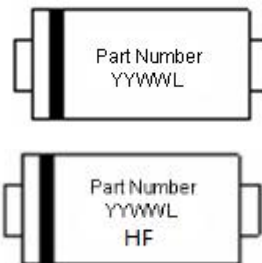
Mechanical Dimensions SMA


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.84	0.094	0.112
B	3.99	4.75	0.157	0.187
C	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
H	0.76	1.52	0.030	0.600

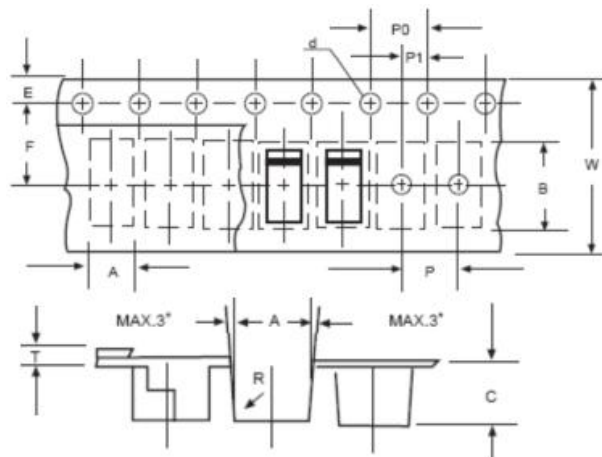
Ordering Information

Device	Package	Shipping
GS1A-GS1M	SMA	5000pcs / reel
GS1ATR-GS1MTR	SMA	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


First row: Part Number (GS1A, GS1B, GS1D, GS1G, GS1J, GS1K, GS1M)
 Second row: YYWWL
 HF is Halogen Free
 YY is the manufacture year,
 WW is the manufacture week code,
 L is the wafer's Lot Number

Carrier Tape Specification SMA


SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC Diode Solutions sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall SMC Diode Solutions be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC Diode Solution assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall SMC Diode Solutions be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC Diode Solutions.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC Diode Solutions.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations..